

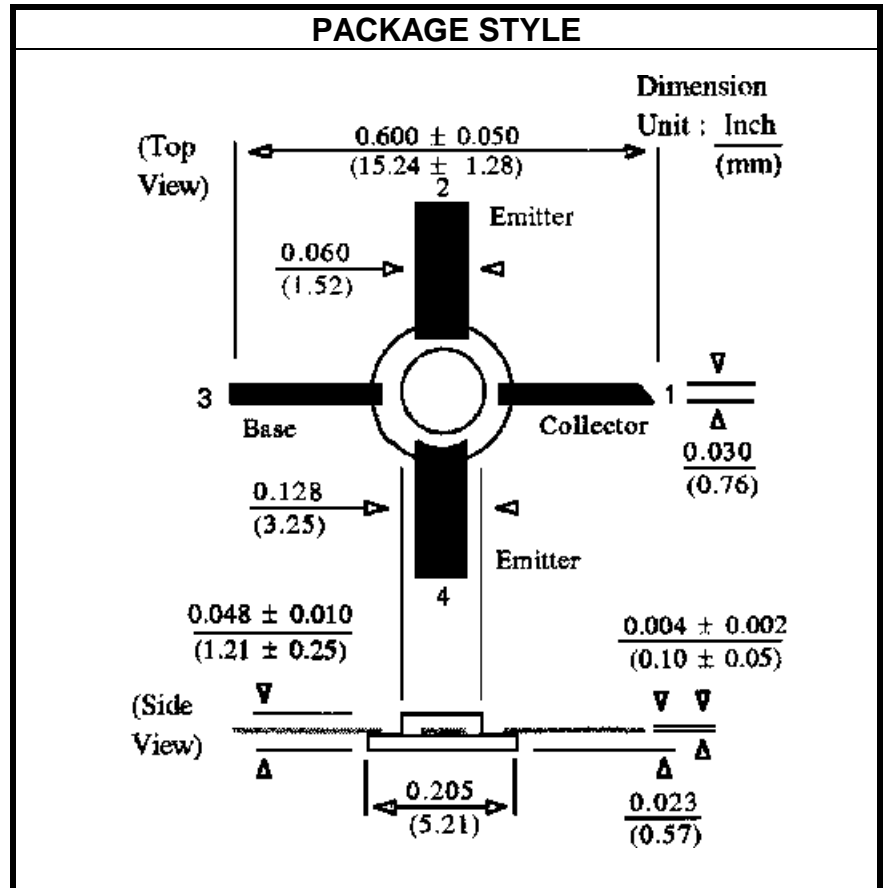
NPN SILICON RF TRANSISTOR

DESCRIPTION:

The **AT64020** is a Common Emitter Device Designed for Medium Power Class C Applications Operating at VHF,UHF Frequencies.

MAXIMUM RATINGS

I_C	120 mA
I_C	180 mA (MAX)
V_{CEO}	15 V
V_{CBO}	25 V
V_{EBO}	1.5 V
T_J	200 °C
T_{STG}	-65 °C to +150 °C


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CBO}	$V_{CB} = 10 V$					400	μA
h_{FE}	$V_{CE} = 8.0 V$	$I_C = 15 mA$		30	110	300	---
f_t	$V_{CE} = 10 V$	$I_C = 60 mA$	$f = 1.0 GHz$		8.0		GHz
$ S_{21} ^2$	$V_{CE} = 10 V$	$I_C = 60 mA$	$f = 1.0 GHz$		15.6		dB
$ S_{21} ^2$	$V_{CE} = 10 V$	$I_C = 60 mA$	$f = 2.0 GHz$		9.0		dB
P_{1dB}	$V_{CE} = 10 V$	$I_C = 75 mA$	$f = 1.0 GHz$		27		dBm
NF	$V_{CE} = 8.0 V$	$I_C = 20 mA$	$f = 1.0 GHz$		1.6		dB